(3 Hours) **Max. marks: 80**

N.B.: (1) Question No. 1 is compulsory.
(2) Solve any three questions from the remaining five questions.
(3) Figures to the right indicate full marks.
(4) Assume suitable data if necessary and mention the same in answer sheet.

Q.1 Attempt any 5 questions. [20]

a) Explain MOSFET as an amplifier.

b) Compare RC coupled, transformer coupled and direct coupled.

c) Explain the effect of source resistance on design of multistage amplifiers.

d) Explain crossover distortion.

e) Explain Barkhausean criterion for sustained oscillations.

f) What are the advantages of negative feedback amplifiers?

Q.2 a) What are the different biasing techniques used to bias D-MOSFET and E-MOSFET. Explain with the help of appropriate diagrams [10]

b) Discuss Darlington pair. What are its primary features? Obtain expression for A_V, A_i and R_i. [10]

Q.3 a) Design a class-B power amplifier with the following specifications: Output power= 8 W, R_L = 8 Ω, V_{CC} = 15 V. [10]

b) Design a two stage RC coupled cascaded amplifier for the following specification $|A_V| \geq 500$, $R_i > 1$ MΩ, $S_i \leq 8$, $V_{o(rms)}$ =3V and f_L = 20 Hz. [10]

Q.4 a) Explain working principle of Wein Bridge oscillator. Derive the expression for its frequency of oscillation and value of gain required for sustained oscillation. [10]

b) Draw the circuit diagram of transformer coupled class A power amplifier and derive the expression for maximum conversion efficiency. [10]

Q.5 a) Design a two stage RC coupled CE-CE amplifier for the following parameters $A_V \geq 2500$, $f \geq 40$ Hz, $S \leq 10$, V_O =2.5. Use transistor BC147A. [10]

b) Explain the concept of negative feedback and explain its effect on gain, input and output impedance in voltage shunt feedback network. [10]

Q.6 Short notes on: (Attempt any four) [20]

a) V-I characteristics of MOSFET
b) LC oscillators
c) Cascode amplifier
d) Current series feedback amplifier
e) Design of heat sink

Transistor type	Pdmax @ 25°C Watts	Icmax @ 25°C Amps	$V_{CE}^{(sat)}$ volts d.c.	V_{CBO} volts d.c.	V_{CEO} (Sus) volts d.c.	V_{CER} (Sus) volts d.c.	V_{CEX} volts d.c.	V_{EBO} volts d.c.	T_j max °C	D.C. current gain min	D.C. current gain typ.	D.C. current gain max.	Small Signal h_{fe} min.	Small Signal h_{fe} typ.	Small Signal h_{fe} max.	V_{BE} max.	θ_{jc} °C/W	Derate above 25°C W/°C
2N 3055	115·5	15·0	1·1	100	60	70	90	7	200	20	50	70	15	50	120	1·8	1·5	0·7
ECN 055	50·0	5·0	1·0	60	50	55	60	5	200	25	50	100	25	75	125	1·5	3·5	0·4
ECN 149	30·0	4·0	1·0	50	40	—	—	8	150	30	50	110	33	60	115	1·2	4·0	0·3
ECN 100	5·0	0·7	0·6	70	60	65	—	6	200	50	90	280	50	90	280	0·9	35	0·03
BC147A	0·25	0·1	0·25	50	45	50	—	6	125	115	180	220	125	220	260	0·9	—	—
2N 525(PNP)	0·225	0·5	0·25	85	30	—	—	—	100	35	—	65	—	45	—	—	—	—
BC147B	0·25	0·1	0·25	50	45	50	—	6	125	200	290	450	240	330	500	0·9	—	—

Transistor type	hie	hoe	hre	θja
BC 147A	2·7 K Ω	18μ ℧	1·5 × 10⁻⁴	0·4°C/mw
2N 525 (PNP)	1·4 K Ω	25μ ℧	3·2 × 10⁻⁴	—
BC 147B	4·5 K Ω	30μ ℧	2 × 10⁻⁴	0·4°C/mw
ECN 100	500 Ω	—	—	—
ECN 149	250 Ω	—	—	—
ECN 055	100 Ω	—	—	—
2N 3055	25 Ω	—	—	—

BFW 11—JFET MUTUAL CHARACTERISTICS

$-V_{GS}$ volts	0·0	0·2	0·4	0·6	0·8	1·0	1·2	1·6	2·0	2·4	2·5	3·0	3·5	4·0
I_{DS} max. mA	10	9·0	8·3	7·6	6·8	6·1	5·4	4·2	3·1	2·2	2·0	1·1	0·5	0·0
I_{DS} typ. mA	7·0	6·0	5·4	4·6	4·0	3·3	2·7	1·7	0·8	0·2	0·0	0·0	0·0	0·0
I_{DS} min. mA	4·0	3·0	2·2	1·6	1·0	0·5	0·0	0·0	0·0	0·0	0·0	0·0	0·0	0·0

N-Channel JFET

Type	V_{DS} max. Volts	V_{DG} max. Volts	V_{GS} max. Volts	P_d max. @25°C	T_j max.	I_{DSS}	g_{mo} (typical)	$-V_p$ Volts	r_d	Derate above 25°C	θ_{ja}
2N3822	50	50	50	300 mW	175°C	2 mA	3000 μ ℧	6	50 KΩ	2 mW/°C	0·59°C/mW
BFW 11 (typical)	30	30	30	300 mW	200°C	7 mA	5600 μ ℧	2·5	50 KΩ	—	0·59° C/mW

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